

Performance

- Technology: 0.25um Power GaN HEMT
- Frequency: 8~12GHz
- Typical Pout : 45dBm(CW)
- Typical Gain: 18dB
- Typical PAE: 28%
- Bias: 28V/3.5A
- Package: Metal Ceramic

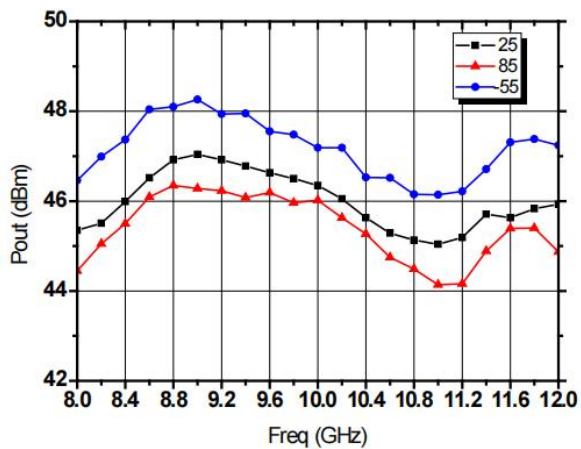


Electrical Specifications (TA=25°C, Vd=28V, Id=3.5A, F: 8~12GHz, Pin=27dBm)

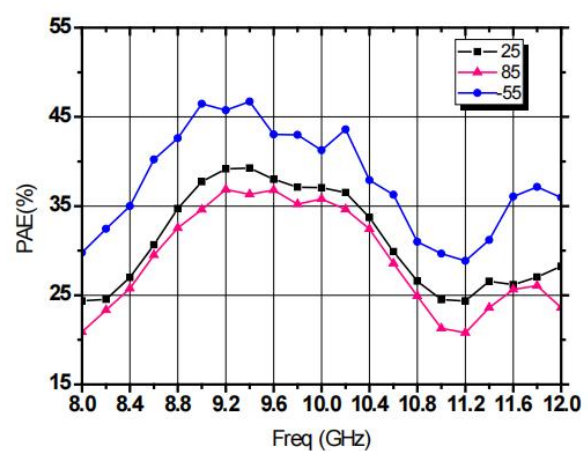
Symbol	Parameter	Min	Typical	Max	Unit
Pout	Output Power	44	45	-	dBm
Gp	Power Gain	17	18	-	dB
η_{add}	Power Added Efficiency	22	28	-	%
ΔGp	Gain Flatness	-1	-	+1	dB
Rth	Thermal Resistance	-	1.3	1.5	°C/W

Test Curves

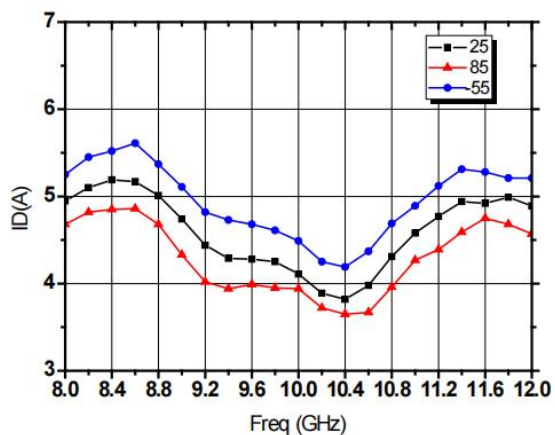
Pout&Freq. @ Different Temp.



PAE&Freq. @ Different Temp.



Id&Freq. @ Different Temp.

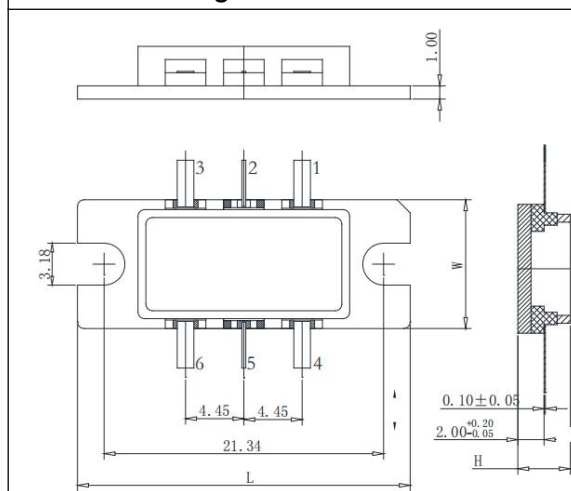


Absolute Max Ratings (TA=25°C)

Symbol	Parameter	Value	Remark
Vd	Drain Voltage	32V	
Vg	Grid Voltage	-5V	
Pd	DC Dissipation	200W	25°C
Tch	Channel Temperature	225°C	【1】
Tm	Mounting Temperature	300°C	1 min, N2 Protection
Tstg	Storage Temperature	-55~175°C	

【1】 Exceeding any one or combination of these limits may cause permanent damage.

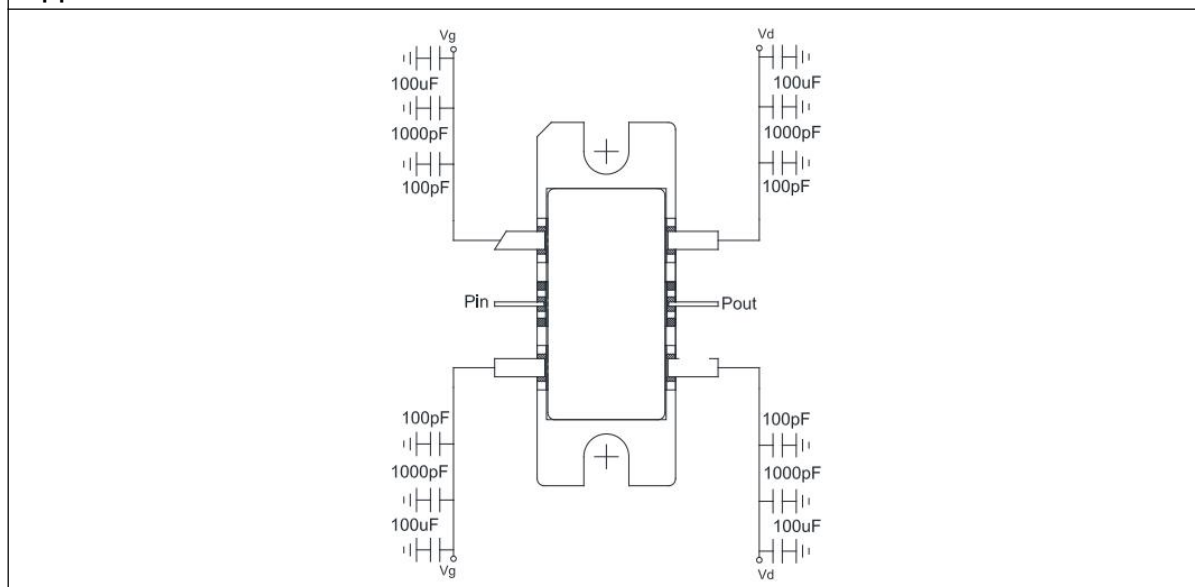
Outline Drawing



Dimension Symbol

Symbol	Value (unit: mm)		
	Min.	Typ.	Max.
H	-	-	4.50
L	25.27	25.4	25.53
W	9.65	9.78	9.91

Application Circuit



Note:

- (1) This product is a power amplifier module, with input and output impedance values of 50 ohms;
- (2) Please strictly follow the sequence of applying negative power first and then positive power.
When removing power, first decrease the leakage voltage and then decrease the gate voltage;
- (3) This product is a high-power device, and attention should be paid to heat dissipation during use.
The higher the shell temperature, the shorter the service life;
- (4) This product is an electrostatic sensitive device, which requires attention to electrostatic protection during storage and use, and requires good grounding during use.